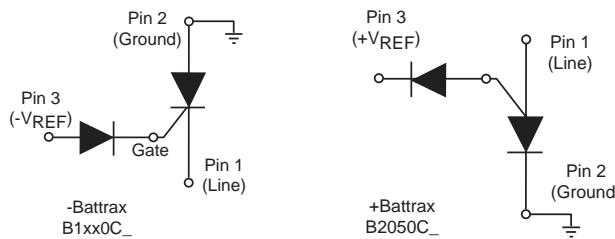


Battrax SLIC Protector

This solid state protection device can be referenced to either a positive or negative voltage source. The B1xx0C_ is for a $-V_{REF}$ and the B2050C_ is for a $+V_{REF}$. Designed using an SCR and a gate diode, the B1xx0C_ Battrax begins to conduct at $| -V_{REF} | + |-1.2 \text{ V}|$ while the B2050C_ Battrax begins to conduct at $| +V_{REF} | + |1.2 \text{ V}|$.

For a diagram of a Battrax application, see Figure 3.38.



Electrical Parameters

Part Number *	V_{DRM} Volts	V_s Volts	V_T Volts	I_{DRM} μAmps	I_{GT} mAmps	I_T Amps	I_H mAmps	C_o pF
B1100C_	$ -V_{REF} + -1.2 \text{ V} $	$ -V_{REF} + -10 \text{ V} $	4	5	100	2.2	100	50
B1160C_	$ -V_{REF} + -1.2 \text{ V} $	$ -V_{REF} + -10 \text{ V} $	4	5	100	2.2	160	50
B1200C_	$ -V_{REF} + -1.2 \text{ V} $	$ -V_{REF} + -10 \text{ V} $	4	5	100	2.2	200	50
B2050C_	$ +V_{REF} + 1.2 \text{ V} $	$ +V_{REF} + 10 \text{ V} $	4	5	50	2.2	50	50

* For individual "CA" and "CC" surge ratings, see table below.

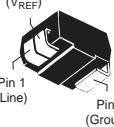
General Notes:

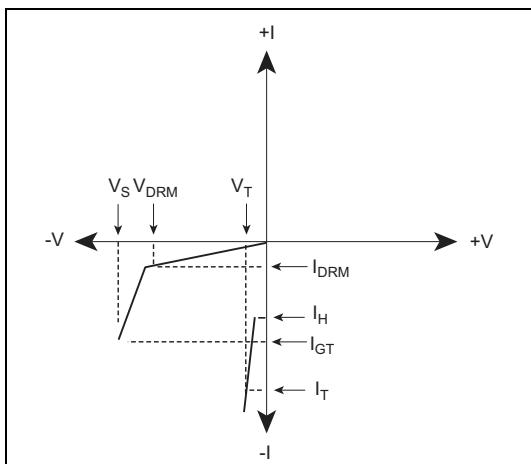
- All measurements are made at an ambient temperature of 25 °C. I_{PP} applies to -40 °C through +85 °C temperature range.
- I_{PP} is a repetitive surge rating and is guaranteed for the life of the product.
- I_{PP} ratings assume $V_{REF} = \pm 48 \text{ V}$.
- V_{DRM} is measured at I_{DRM} .
- V_s is measured at 100 V/ μs .
- Off-state capacitance (C_o) is measured at 1 MHz with a 2 V bias and is a typical value. "CC" product is approximately 2x the listed value.
- Positive Battrax information is preliminary data.
- V_{REF} maximum value for the negative Battrax is -200 V.
- V_{REF} maximum value for the positive Battrax is 110 V.

Surge Ratings

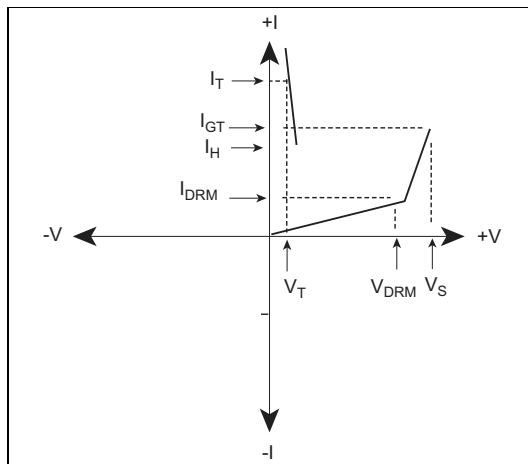
Series	I_{PP} 2x10 μs Amps	I_{PP} 8x20 μs Amps	I_{PP} 10x160 μs Amps	I_{PP} 10x560 μs Amps	I_{PP} 10x1000 μs Amps	I_{TSM} 60 Hz Amps	di/dt Amps/ μs
A	150	150	90	60	50	20	500
C	500	400	200	150	100	50	500

Thermal Considerations

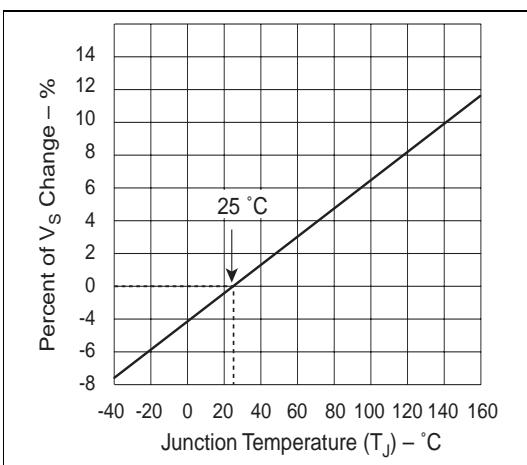
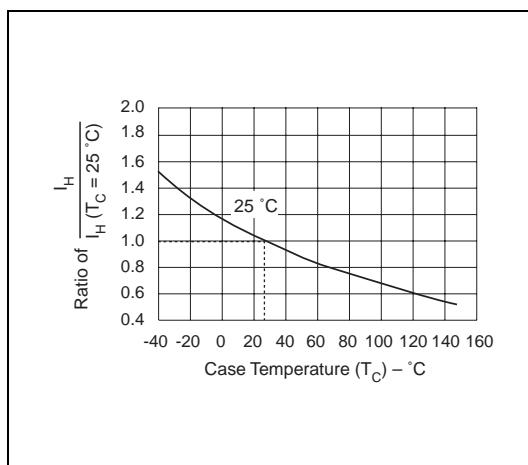
Package	Symbol	Parameter	Value	Unit
 Modified DO-214AA	T_J	Operating Junction Temperature Range	-40 to +150	°C
	T_S	Storage Temperature Range	-65 to +150	°C
	$R_{\theta JA}$	Thermal Resistance: Junction to Ambient	85	°C/W



V-I Characteristics for Negative Battrax



V-I Characteristics for Positive Battrax

Normalized V_S Change versus Junction Temperature

Normalized DC Holding Current versus Case Temperature